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**Serial N . 08/807,737**

# INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

**Applicant: Hisashi OHTANI et al.**

**Filing Date: February 27, 1997**

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## U.S. PATENT DOCUMENTS

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FORERUNNERS DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	<u>Translation</u>	
						Yes	No
ML	3-280420	12/11/91	Japan	—	—	X	

001	Murarka, "Silicides for VLSI Applications", pp. 82 and 112
002	Stoemenos et al., "Crystallization of Amorphous Silicon by Reconstructive Transformation Utilizing Gold", Appl. Phys. Lett. Vol. 58, No. 11, March 18, 1991, pp. 1196-1198
003	Hayzelden et al., "Silicide Formation and Silicid-Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films", J. Appl. Phys., Vol. 73, No. 12, June 15, 1993, pp. 8279-8289
004	Kuznetsov et al., "Enhanced Solid Phase Epitaxial Recrystallization of Amorphous Silicon due to Nickel Silicide Precipitation Resulting from Ion Implantation and Annealing", Nuclear Instruments and Methods in Physics Research B80/81, (1993), pp. 990-993
005	Kawazu et al., "Initial Stage of the Interfacial Reaction between Nickel and Hydrogenated Amorphous Silicon", Japanese Journal of Applied Physics, Vol. 29, No. 4, April 1990, pp. 729-738
006	Batstone et al., "Microscopic Processes in Crystallization", Solid State Phenomena, Vols. 37-38, (1994), pp. 257-268

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